AMENDMENTS TO THE SPECIFICATION

Please replace the title of the invention with:

Light-emitting device having reflective layer formed under electrode

Please insert the paragraphs as follows between paragraph [0014] and the subtitle "DETAILED DESCRIPTION":

Fig. 5 is a schematically structural diagram of an embodiment according to the present invention.

Figs. 6a-6c are schematically structural diagrams showing the contact at rough surface according to the present invention.

Fig. 7 is a schematically structural diagram showing the contact of the reflective layer to the semiconductor layer of an embodiment according to the present invention.

Please replace paragraph [0016] with the following amended paragraph:

The substrate 31 is a conductive material, such as n-type GaAs or GaN, and the DBR 32 is composed of multi-layered reflective structures, such as AlAs and GaAs, for reflecting light. The structure of the active layer 33 is homostructure, single heterostructure, double heterostructure (DH), or multiple quantum well (MQW). If the structure of the active layer 33 is double heterostructure, it can be composed of an n-type AlGaInP lower cladding layer, an AlGaInP active layer, and a p-type AlGaInP upper cladding layer. Since the various structures of the active layer are known in the prior art, no more will be described in this paper. The p-type semiconductor layer 34 is an ohmic contact layer composed of a plurality of p-type III-V compound layers, such as Mg or Zn doped GaN, AlGaAs, AlGaInP, or GaAsP. The p-type semiconductor layer comprising a plurality of p-type III-V compound layers is schematically shown in Fig. 5, for example. The p-type electrode 35 and the n-type electrode 36 are metal

electrodes for wire bonding.

Please replace paragraph [0017] with the following amended paragraph:

The reflective layer 38 is a conductive layer with high reflectivity, such as silver (Ag), aluminum (Al), gold (Au), chromium (Cr), platinum (Pt), or rhodium (Rh), and the reflective layer 38 can be a single-layer or multi-layer structure. The reflective layer comprising a multi-layer structure is schematically shown in Fig. 5, for example. The reflective layer 38 is used for reflecting light from the active layer 33 to surroundings without being absorbed by the p-type electrode 35. In addition, the reflective layer 38 and the p-type semiconductor layer 34 can contact at a rough surface., Tthe rough surface results from the etching process and may be formed to haveing an incline or a curved structure with a specific reflective angle to enhance the reflective layer 38, as shown in Fig.6, for example. The reflective layer 38 can also be a scattering layer, such as a transparent conductive material comprising a plurality of diffusers, for partially reflecting light from the active layer 33 to reduce light being absorbed by the p-type electrode 35. The scattering layer has a more than 50% scattering rate.

Please replace paragraph [0019] with the following amended paragraph:

In the second embodiment, the substrate 41 is a nonconductive material, such as sapphire, and the DBR 42, the active layer 43, and the p-type semiconductor layer 44 are similar to those in the first embodiment. The n-type semiconductor layer 47 is an ohmic contact layer composed of a plurality of n-type III-V compound layers, such as undoped GaN, Si doped GaN, AlGaAs, AlGaInP, or GaAsP. The p-type and n-type semiconductor layers comprising a plurality of III-V compound layers are schematically shown in Fig. 7, for example. The p-type electrode 45 and the n-type electrode 46 are metal electrodes for wire bonding

Please replace paragraph [0020] with the following amended paragraph:

The first reflective layer 48 and the second reflective layer 49 are also conductive layers with high reflectivity, such as silver (Ag), aluminum (Al), gold (Au), chromium (Cr), platinum (Pt), or rhodium (Rh), and the first reflective layer 48 and the second reflective layer 49 can be single-layer or multi-layer structures. The reflective layers comprising a multi-layer structure are schematically shown in Fig. 7, for example. The first reflective layer 48 and the second reflective layer 49 are used for reflecting light from the active layer 43 to surroundings without being absorbed by the p-type electrode 45 and the n-type electrode 46. In addition, the reflective layers 48, 49 and the p-type and n-type semiconductor layers 44, 47 can contact at a rough surface. The rough surface results from the etching process and may be formed to having an incline or a curved structure with a specific reflective angle to enhance the reflective layers 48, 49, similar to those shown in Figs. 6a-6c, for example. The reflective layers 48, 49 can also be a scattering layer, such as a transparent conductive material comprising a plurality of diffusers, for partially reflecting light from the active layer 43 to reduce light being absorbed by the p-type electrode 45 and the n-type electrode 46. The scattering layer has a more than 50% scattering rate.